

# 1 Watt Ku Band Packaged Amplifier

TGA2903-EPU-SG



### **Preliminary Measured Performance**

Bias Conditions: Vd=7 V Id=430 mA



# **Key Features and Performance**

- Surface Mountable
- Frequency Range: 13 17 GHz
- 30 dBm Midband Pout
- 30 dB Nominal Gain
- 15 dB Typical Input Return Loss
- 8 dB Typical Output Return Loss
- 0.5µm pHEMT Technology
- Bias Conditions: 7 V. 430 mA
- Available in Tape & Reel or Waffle Pack
- Package dimensions: 9.4 x 6.4 x 0.1 mm (370 x 250 x 4 mils)

# **Primary Applications**

- VSAT
- Point to Point

Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice.





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#### TABLE I MAXIMUM RATINGS

Symbol	Parameter <u>1</u> /	Value	Notes
VD	Drain Voltage	8 V	<u>2</u> /
$V_{G}$	Gate Voltage Range	-5V to 0V	
I <sub>D</sub>	Drain Current (Quiescent)	591 mA	<u>2</u> /
I <sub>G</sub>	Gate Current	14 mA	
P <sub>IN</sub>	Input Continuous Wave Power	17 dBm	<u>2</u> /
PD	Power Dissipation	TBD	<u>2</u> /
Т <sub>СН</sub>	Operating Channel Temperature	150 <sup>0</sup> C	<u>3</u> / <u>4</u> /
Τ <sub>M</sub>	Mounting Temperature (30 Seconds)	320 <sup>0</sup> C	
T <sub>STG</sub>	Storage Temperature	-65 to 150 <sup>0</sup> C	

- <u>1</u>/ These ratings represent the maximum operable values for this device.
- <u>2</u>/ Combinations of drain voltage, drain current, input power and output power shall not exceed P<sub>D</sub>.
- $\underline{3}$  / These ratings apply to each individual FET.
- <u>4</u>/ Junction operating temperature will directly affect the device medain time to failure (T<sub>M</sub>). For maximum life, it is recommended that junction temperatures be maintained at the lowest possible levels.

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#### TABLE II RF CHARACTERIZATION TABLE $(T_A = 25^{\circ}C, Nominal)$ $(Vd = 7V, Id = 430mA \pm 5\%)$

SYMBOL	PARAMETER	TEST	LIMITS		5	UNITS
		CONDITION	MIN	TYP	MAX	
Gain	Small Signal Gain	F = 13-17GHz		30		dB
IRL	Input Return Loss	F = 13-17GHz		15		dB
ORL	Output Return Loss	F = 13-17GHz		10		dB
PWR	Output Power @ P1dB	F = 13-17GHz		30		dBm
PAE	Power Added Efficiency @ P1dB	F = 13-17GHz		22		%

Note: Table III Lists the RF Characteristics of typical devices as determined by fixtured measurements.

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**Typical Fixtured Performance** 



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# Package Pinout Diagram



GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.

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**Mechanical Drawing** 

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# **Recommended PWB Land Pattern**



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